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NOT FOR FILING**

Attorney Docket No. YAO-3950US2
PATENT

In re Application of :
Yoshihisa Nagano et al. : Group Art Unit: 2815
Serial No.: 10/170,168. : Examiner: Jose R. Diaz
Filed: June 12, 2002 :
For: SEMICONDUCTOR DEVICE AND METHOD FOR FABRICATING THE SAME

AMENDMENT UNDER 37 C.F.R. § 1.111

IN THE CLAIMS:

Please amend claims 28 and add new claim 47 as follows.

1. (Currently amended) A method for fabricating a semiconductor device, comprising the step of:

sequentially forming a lower electrode, a dielectric film comprising [either dielectric material having a high dielectric constant or] a ferroelectric [material] film, and an upper electrode on a supporting substrate [having an integrated], thereby forming a capacitor;

forming a first interlayer insulating film provided so as to cover the capacitor;

forming a first contact hole in the first interlayer insulating film;